

## P-Channel 20 V (D-S) MOSFET

MOSFET PRODUCT SUMMARY			
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ.)
- 20	0.112 at V <sub>GS</sub> = - 4.5 V	- 3.1	3.3 nC
	0.142 at V <sub>GS</sub> = - 2.5 V	- 2.7	

### FEATURES

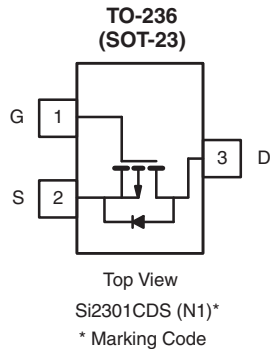
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET<sup>®</sup> Power MOSFET
- Compliant to RoHS Directive 2002/95/EC



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**  
Available

### APPLICATIONS

- Load Switch



Ordering Information: Si2301CDS-T1-E3 (Lead (Pb)-free)  
Si2301CDS-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C, unless otherwise noted)			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	- 20	V
Gate-Source Voltage	V <sub>GS</sub>	± 8	
Continuous Drain Current (T <sub>J</sub> = 150 °C)	I <sub>D</sub>	T <sub>C</sub> = 25 °C	- 3.1
		T <sub>C</sub> = 70 °C	- 2.5
		T <sub>A</sub> = 25 °C	- 2.3 <sup>b, c</sup>
		T <sub>A</sub> = 70 °C	- 1.8 <sup>b, c</sup>
Pulsed Drain Current	I <sub>DM</sub>	- 10	A
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	
		T <sub>A</sub> = 25 °C	- 0.72 <sup>b, c</sup>
Maximum Power Dissipation	P <sub>D</sub>	T <sub>C</sub> = 25 °C	1.6
		T <sub>C</sub> = 70 °C	1.0
		T <sub>A</sub> = 25 °C	0.86 <sup>b, c</sup>
		T <sub>A</sub> = 70 °C	0.55 <sup>b, c</sup>
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>b, d</sup>	≤ 5 s	R <sub>thJA</sub>	120	145	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R <sub>thJF</sub>	62	78	

Notes:

- Based on T<sub>C</sub> = 25 °C.
- Surface mounted on 1" x 1" FR4 board.
- t = 5 s.
- Maximum under steady state conditions is 175 °C/W.

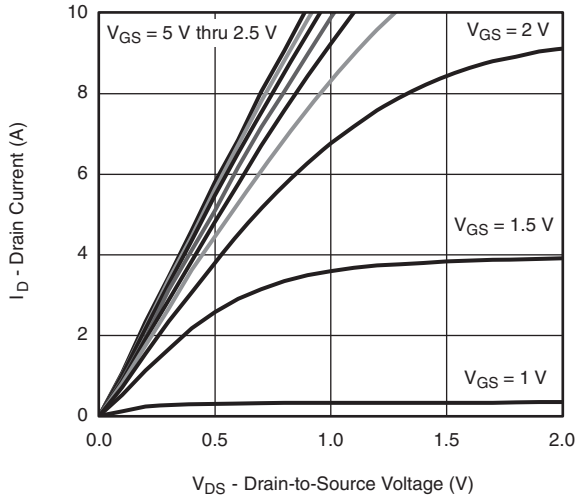
MOSFET SPECIFICATIONS ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-20			V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = -250\text{ }\mu\text{A}$		-18		mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			2.2		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-0.4		-1	V
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 8\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}$			-1	$\mu\text{A}$
		$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			-10	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \leq -5\text{ V}, V_{GS} = -4.5\text{ V}$	-6			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = -4.5\text{ V}, I_D = -2.8\text{ A}$		0.090	0.112	$\Omega$
		$V_{GS} = -2.5\text{ V}, I_D = -2.0\text{ A}$		0.110	0.142	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = -5\text{ V}, I_D = -2.8\text{ A}$		9.5		S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = -10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		405		pF
Output Capacitance	$C_{oss}$			75		
Reverse Transfer Capacitance	$C_{rss}$			55		
Total Gate Charge	$Q_g$	$V_{DS} = -10\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -3\text{ A}$		5.5	10	nC
				3.3	6	
Gate-Source Charge	$Q_{gs}$	$V_{DS} = -10\text{ V}, V_{GS} = -2.5\text{ V}, I_D = -3\text{ A}$		0.7		
Gate-Drain Charge	$Q_{gd}$			1.3		
Gate Resistance	$R_g$	$f = 1\text{ MHz}$		6.0		$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -10\text{ V}, R_L = 10\text{ }\Omega$ $I_D = -1\text{ A}, V_{GEN} = -4.5\text{ V}, R_g = 1\text{ }\Omega$		11	20	ns
Rise Time	$t_r$			35	60	
Turn-Off Delay Time	$t_{d(off)}$			30	50	
Fall Time	$t_f$			10	20	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$			-1.3	A
Pulse Diode Forward Current <sup>a</sup>	$I_{SM}$				-10	
Body Diode Voltage	$V_{SD}$	$I_S = -0.7\text{ A}$		-0.8	-1.2	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = -3.0\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		30	50	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			25	50	nC
Reverse Recovery Fall Time	$t_a$			15		ns
Reverse Recovery Rise Time	$t_b$			15		

Notes:

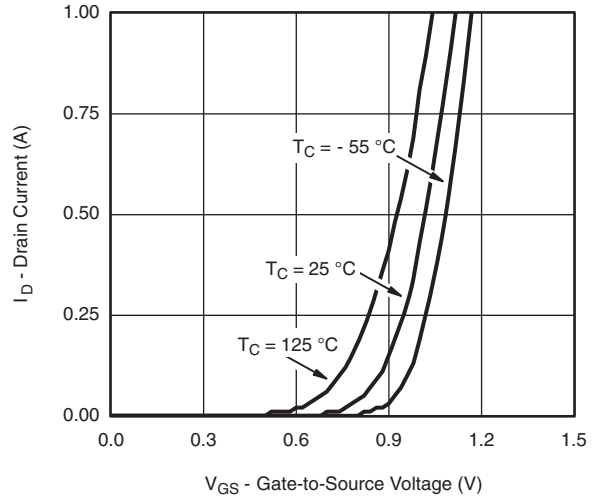
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



**Output Characteristics**



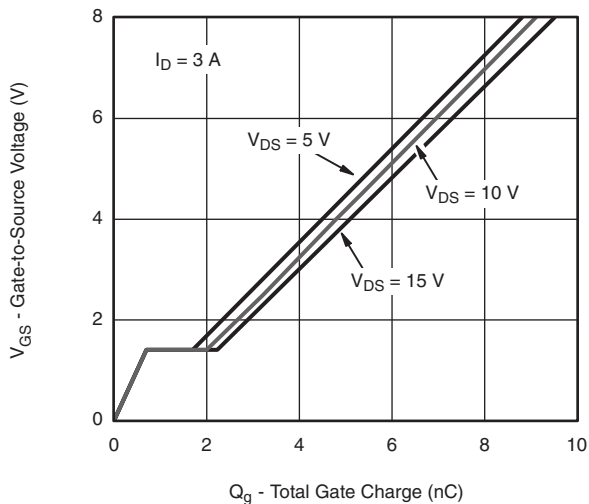
**Transfer Characteristics**



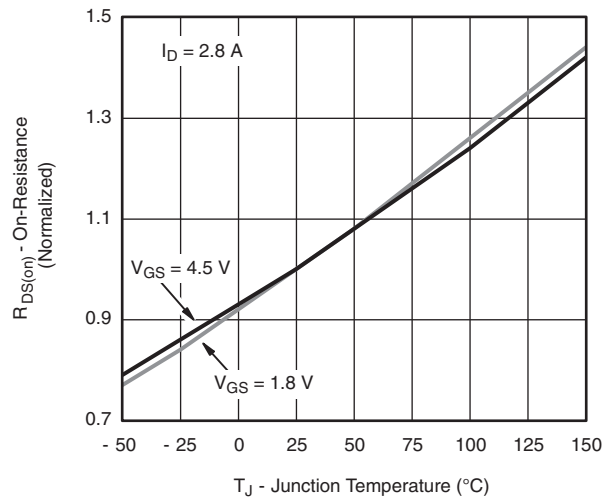
**On-Resistance vs. Drain Current and Gate Voltage**



**Capacitance**



**Gate Charge**



**On-Resistance vs. Junction Temperature**

## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power



\*  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

Safe Operating Area

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



**Normalized Thermal Transient Impedance, Junction-to-Ambient**



**Normalized Thermal Transient Impedance, Junction-to-Foot**

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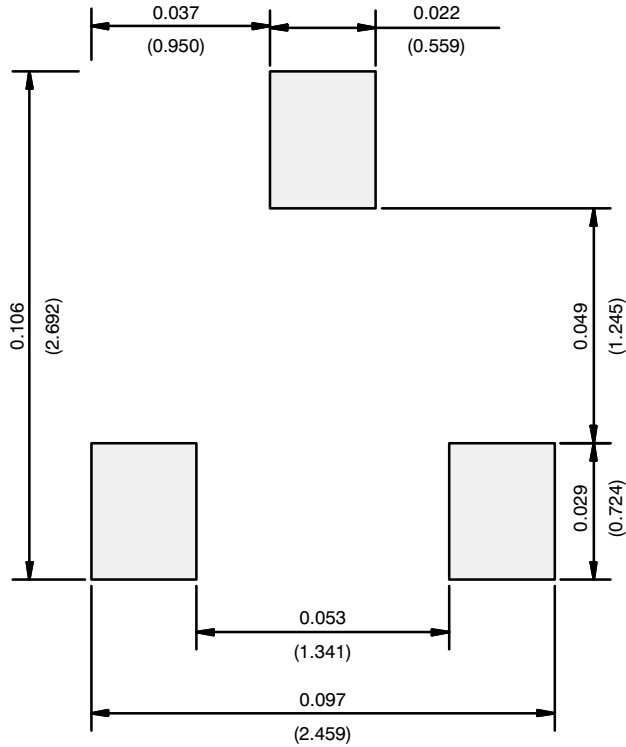
## SOT-23 (TO-236): 3-LEAD



Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	0.89	1.12	0.035	0.044
A <sub>1</sub>	0.01	0.10	0.0004	0.004
A <sub>2</sub>	0.88	1.02	0.0346	0.040
b	0.35	0.50	0.014	0.020
c	0.085	0.18	0.003	0.007
D	2.80	3.04	0.110	0.120
E	2.10	2.64	0.083	0.104
E <sub>1</sub>	1.20	1.40	0.047	0.055
e	0.95 BSC		0.0374 Ref	
e <sub>1</sub>	1.90 BSC		0.0748 Ref	
L	0.40	0.60	0.016	0.024
L <sub>1</sub>	0.64 Ref		0.025 Ref	
S	0.50 Ref		0.020 Ref	
q	3°	8°	3°	8°

ECN: S-03946-Rev. K, 09-Jul-01  
 DWG: 5479

## RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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